

Amendments to the CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended): A method for forming a pattern over a substrate, comprising:
 - providing a master having at least one opening;
 - providing a substrate having an etching layer formed thereon;
 - locating the master over the etching layer, the master being separated from the substrate at a distance;
 - filling a resist in the at least one opening of the master; and
 - separating the master from the substrate to leave the resist on the substrate,wherein the master is separated from the substrate ~~at a distance~~ by a few micrometers (μm) during filling the resist in opening of the ~~master~~ master.
2. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - contacting a resist supplying roll to the master; and
 - filling the resist in the at least one opening of the master by rotating the resist supplying roll over the at least one opening of the master.
3. (Original): The method of claim 1, wherein the filling a resist in the at least one opening of the master comprises:
 - applying the resist on the master; and
 - planarizing the applied resist on the surface of the master by using a doctor blade.
4. (Canceled)
5. (Original): The method of claim 1, wherein the etching layer is a metal layer.

6. (Original): The method of claim 1, wherein the etching layer is an insulating layer.

7. (Original): The method of claim 6, wherein the insulating layer is formed of one of SiO_x or SiN_x.

8. (Original): The method of claim 1, wherein the etching layer is a semiconductor layer.

9. (Original): The method of claim 1, further comprising hardening the resist.

10. (Currently Amended): A method for forming a pattern over a substrate, comprising:

- providing a master having at least one opening;
- providing a substrate having an etching layer formed thereon;
- placing the master over an area corresponding to the etching layer to be etched, the master being separated from the substrate at a distance;
- applying a resist on the master;
- planarizing the applied resist on the surface of the master and filling the resist in the at least one opening by using a doctor blade;
- hardening the planarized resist; and
- forming a resist pattern on the etching layer by separating the master from the substrate, wherein the master is separated from the substrate ~~at a distance~~ by a few micrometers (μm) during filling the resist in opening of the ~~master~~ master.

11. (Canceled).

12. (Currently Amended): A method for forming a pattern over a substrate, comprising:

- providing a master having at least one opening

providing a substrate having an etching layer formed thereon;
placing the master over the etching layer, the opening of the master being corresponding to the etching region to be etched;
contacting a resist supplying roll on the master to fill the resist in the at least one opening of the master, the master being separated from the substrate at a distance;
hardening the filled resist in the at least one opening of the master; and
forming a resist pattern on the etching layer by separating mechanically the master from the substrate,
wherein the master is separated from the substrate ~~at a distance~~ by a few micrometers (μm) during filling the resist in opening of the ~~mater~~ master.

13. (Canceled).